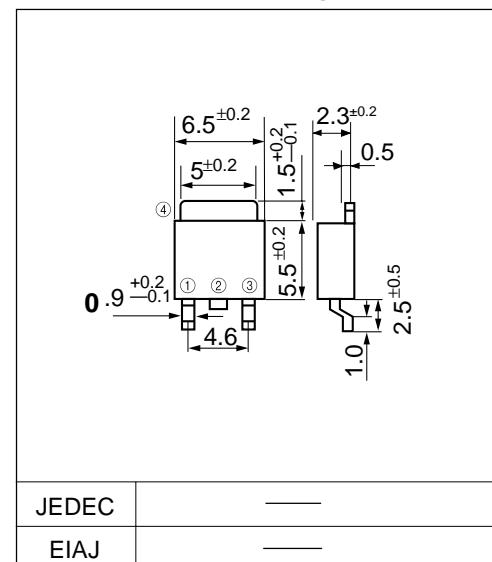


SCHOTTKY BARRIER DIODE

■ Outline drawings, mm



JEDEC

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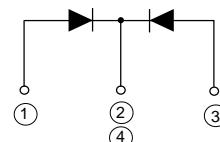
■ Features

- Surface mount device
- Low VF
- Super high speed switching
- High reliability by planer design

■ Applications

- High speed power switching

■ Connection diagram



■ Maximum ratings and characteristics

- Absolute maximum ratings

Item	Symbol	Conditions	Rating	Unit
Repetitive peak reverse voltage	V _{RRM}		90	V
Non-repetitive peak reverse voltage	V _{RSM}	t _w =500ns, duty=1/40	90	V
Average output current	I _O	Square wave, duty=1/2 T _c =100°C	5.0*	A
Surge current	I _{FSM}	Sine wave 10ms	60	A
Operating junction temperature	T _j		-40 to +150	°C
Storage temperature	T _{stg}		-40 to +150	°C

* Average forward current of centertap full wave connection

- Electrical characteristics (Ta=25°C Unless otherwise specified)

Item	Symbol	Conditions	Max.	Unit
Forward voltage drop	V _{FM}	I _{FM} =2.5A	0.9	V
Reverse current	I _{RRM}	V _R =V _{RRM}	5.0	mA
Thermal resistance	R _{th(j-c)}	Junction to case	10	°C/W

■ Characteristics

